



PJT7603

Complementary Enhancement Mode MOSFET – ESD Protected

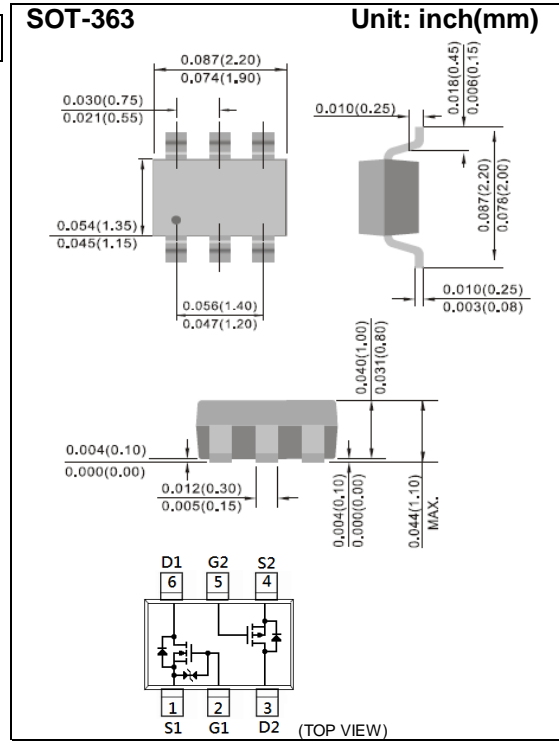
Voltage 50 / -60V **Current** 0.4A / -0.25A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-363 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0002 ounces, 0.006 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| PARAMETER | SYMBOL | N-Ch LIMIT | P-Ch LIMIT | UNITS | |
|--|-----------------|---------------------------------|------------|------------------|----------------------|
| Drain-Source Voltage | V_{DS} | 50 | -60 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | ± 20 | V | |
| Continuous Drain Current | I_D | 400 | -250 | mA | |
| Pulsed Drain Current (Note 4) | I_{DM} | 1200 | -900 | mA | |
| Power Dissipation | P_D | $T_a=25^\circ\text{C}$ | | 350 | mW |
| | | Derate above 25°C | | 2.8 | mW/ $^\circ\text{C}$ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55~150 | | $^\circ\text{C}$ | |
| Typical Thermal resistance | $R_{\theta JA}$ | | | 357 | $^\circ\text{C/W}$ |
| - Junction to Ambient (Note 3) | | | | | |



PJT7603

N-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|--|------|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D = 250uA | 50 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D = 250uA | 0.5 | 0.9 | 1.0 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} = 10V, I _D = 500mA | - | 1.2 | 1.5 | Ω |
| | | V _{GS} = 4.5V, I _D = 200mA | - | 1.3 | 2.5 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 50V, V _{GS} =0V | - | - | 1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±10 | uA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =25V, I _D =500mA, V _{GS} =4.5V | - | 0.95 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.34 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 0.32 | - | |
| Input Capacitance | C _{iss} | V _{DS} =25V, V _{GS} =0V, f=1.0MHZ | - | 36 | - | pF |
| Output Capacitance | C _{oss} | | - | 11 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 6.6 | - | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} =25V, I _D =500mA, V _{GS} =10V, R _G =6Ω (Note 1,2) | - | 2.3 | - | ns |
| Turn-On Rise Time | t _r | | - | 20 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 7 | - | |
| Turn-Off Fall Time | t _f | | - | 20 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | 400 | mA |
| Diode Forward Voltage | V _{SD} | I _S = 500mA, V _{GS} =0V | - | 0.9 | 1.5 | V |

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.



PJT7603

P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS |
|---|---------------------|---|------|------|------|-------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =-250uA | -60 | - | - | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =-250uA | -1.0 | -1.5 | -2.5 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =-10V, I _D =-500mA | - | 2.4 | 4 | Ω |
| | | V _{GS} =-4.5V, I _D =-200mA | - | 2.7 | 6 | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-48V, V _{GS} =0V | - | - | -1 | uA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| Dynamic (Note 5) | | | | | | |
| Total Gate Charge | Q _g | V _{DS} =-25V, I _D =-100mA, V _{GS} =-4.5V | - | 1.1 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.3 | - | |
| Gate-Drain Charge | Q _{gd} | | - | 0.2 | - | |
| Input Capacitance | C _{iss} | V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ | - | 51 | - | pF |
| Output Capacitance | C _{oss} | | - | 15 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 2.2 | - | |
| Turn-On Delay Time | td _(on) | V _{DD} =-25V, I _D =-100mA, V _{GS} =-10V, R _G =6Ω (Note 1,2) | - | 4.8 | - | ns |
| Turn-On Rise Time | tr | | - | 19 | - | |
| Turn-Off Delay Time | td _(off) | | - | 52 | - | |
| Turn-Off Fall Time | tf | | - | 32 | - | |
| Drain-Source Diode | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | --- | - | - | -250 | mA |
| Diode Forward Voltage | V _{SD} | I _S =-500mA, V _{GS} =0V | - | -0.9 | -1.5 | V |



PJT7603

N-Channel TYPICAL CHARACTERISTIC CURVES

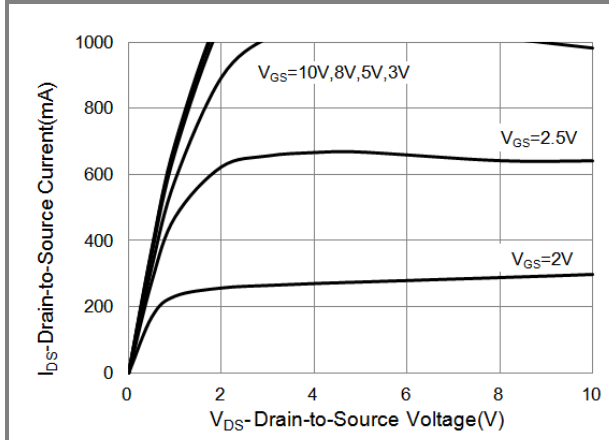


Fig.1 On-Region Characteristics

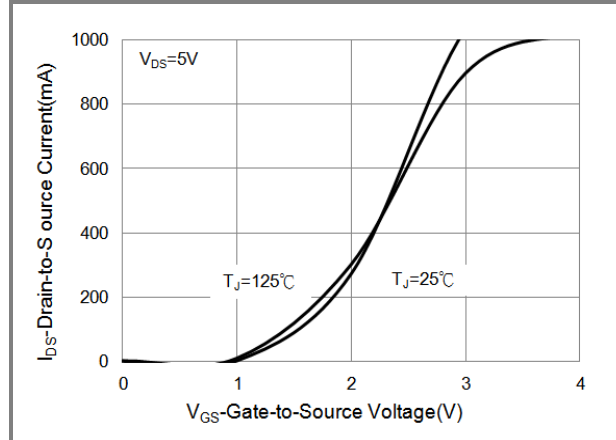


Fig.2 Transfer Characteristics

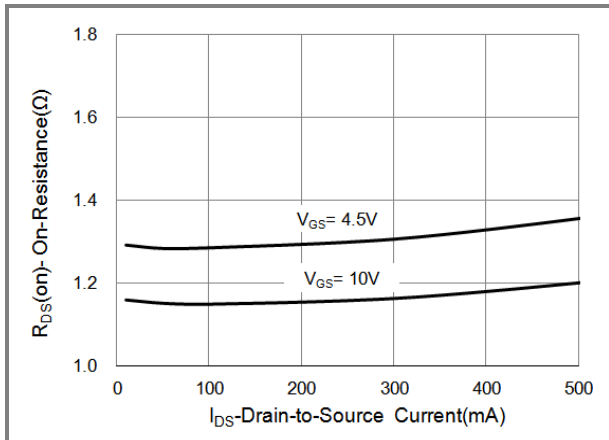


Fig.3 On-Resistance vs. Drain Current

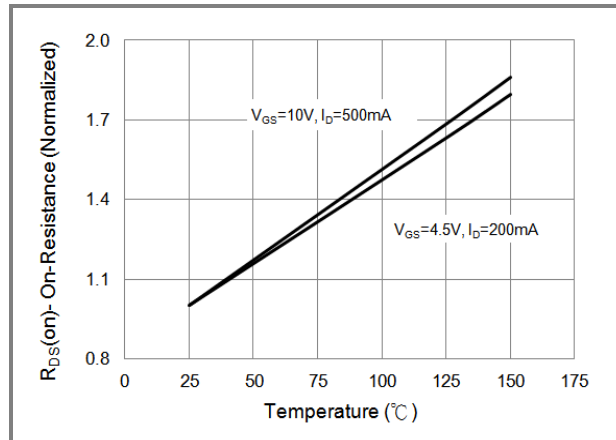


Fig.4 On-Resistance vs. Junction temperature

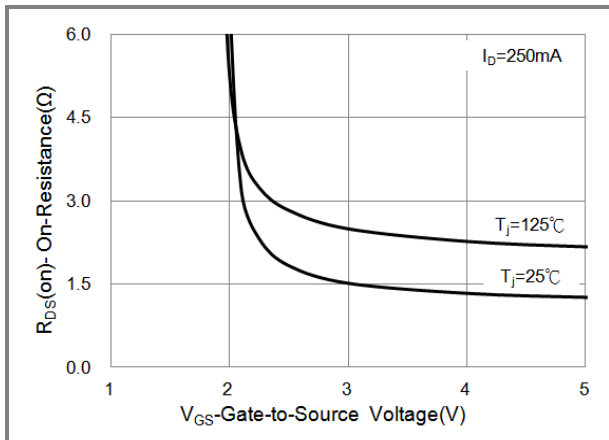


Fig.5 On-Resistance Variation with VGS.

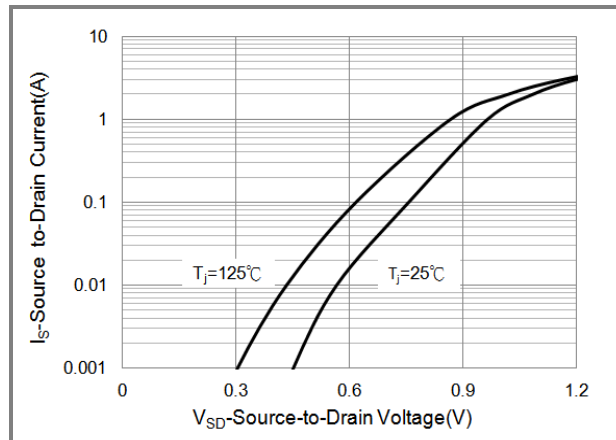


Fig.6 Body Diode Characteristics



PJT7603

N-Channel TYPICAL CHARACTERISTIC CURVES

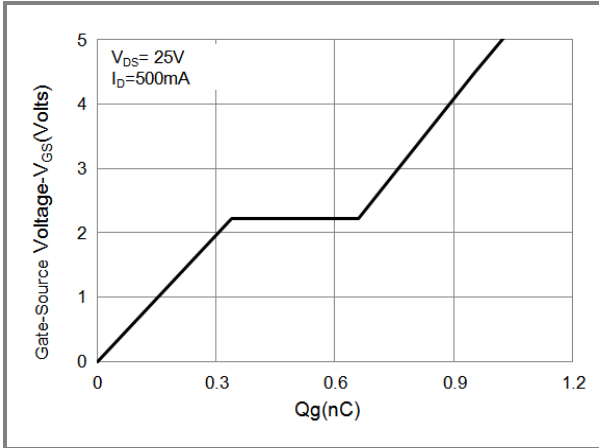


Fig.7 Gate-Charge Characteristics

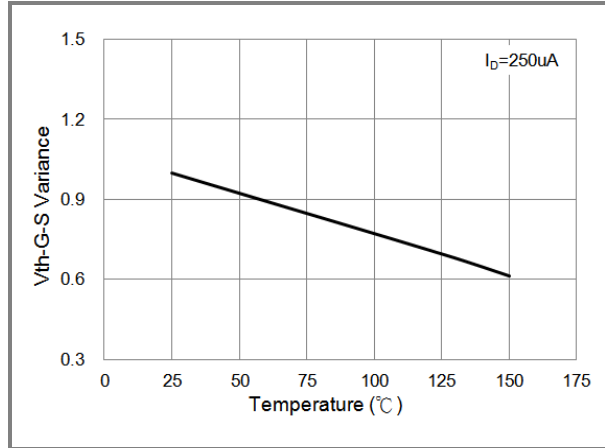


Fig.8 Threshold Voltage Variation with Temperature.

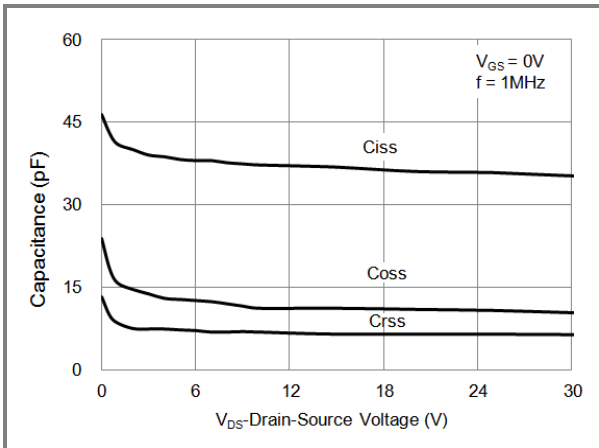


Fig.9 Capacitance vs. Drain-Source Voltage.



PJT7603

P-Channel TYPICAL CHARACTERISTIC CURVES

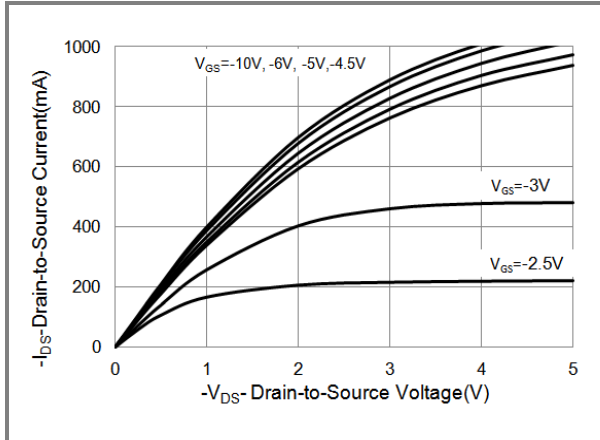


Fig.1 On-Region Characteristics

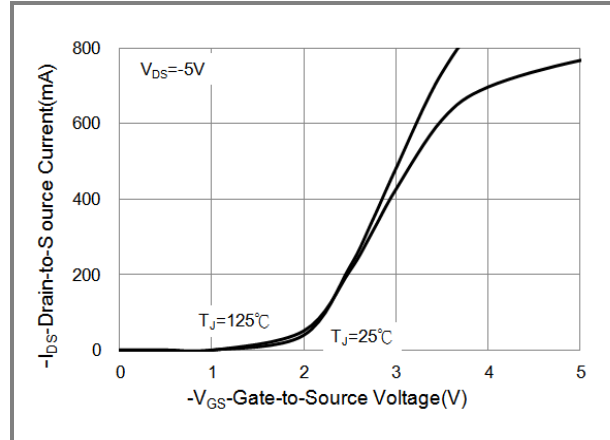


Fig.2 Transfer Characteristics

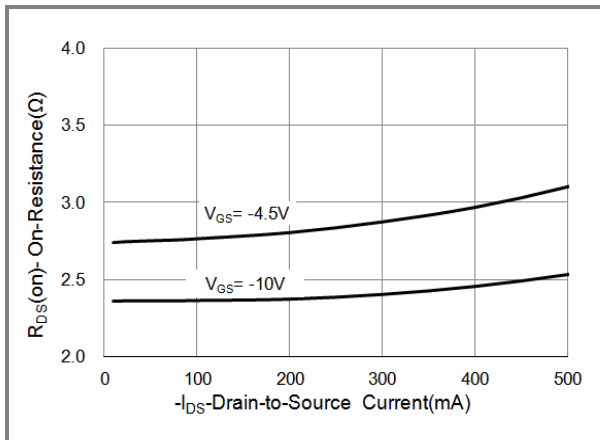


Fig.3 On-Resistance vs. Drain Current

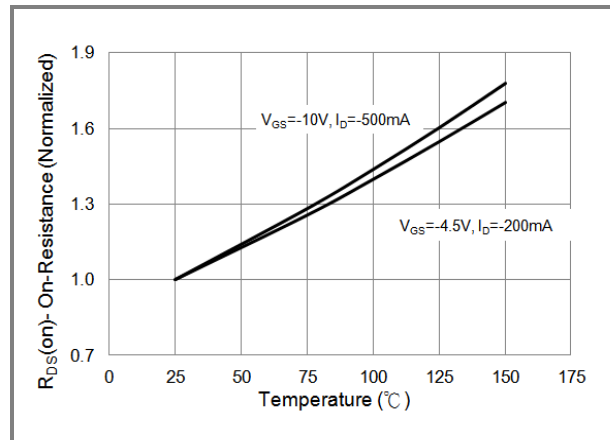


Fig.4 On-Resistance vs. Junction temperature

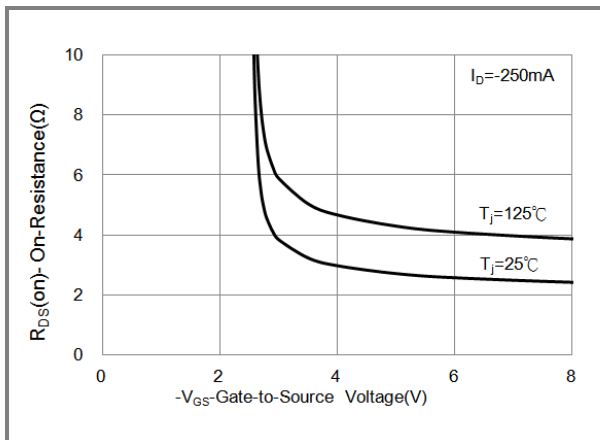


Fig.5 On-Resistance Variation with V_{G_S} .

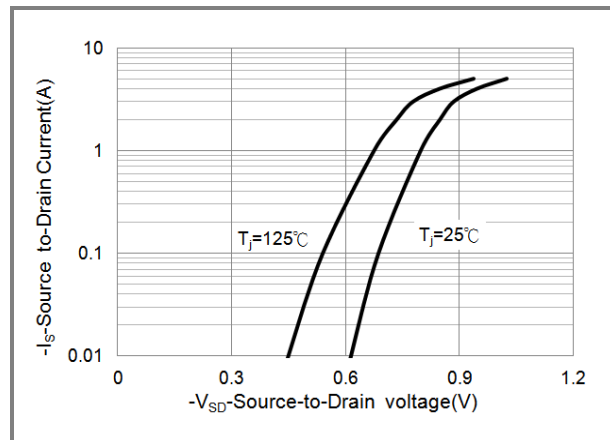


Fig.6 Body Diode Characteristics



PJT7603

P-Channel TYPICAL CHARACTERISTIC CURVES

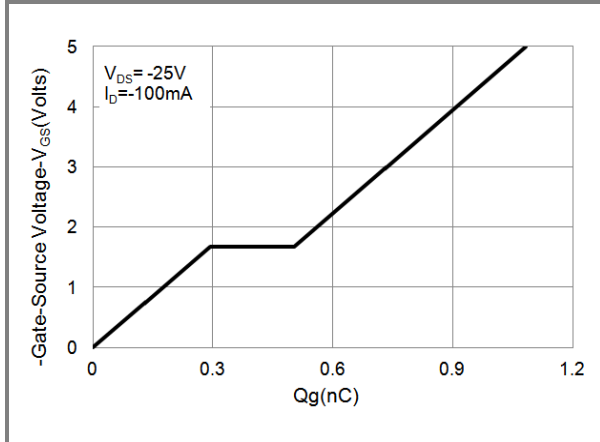


Fig.7 Gate-Charge Characteristics

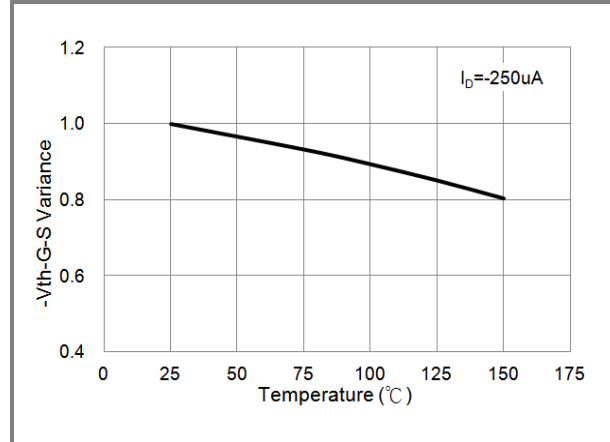


Fig.8 Threshold Voltage Variation with Temperature.

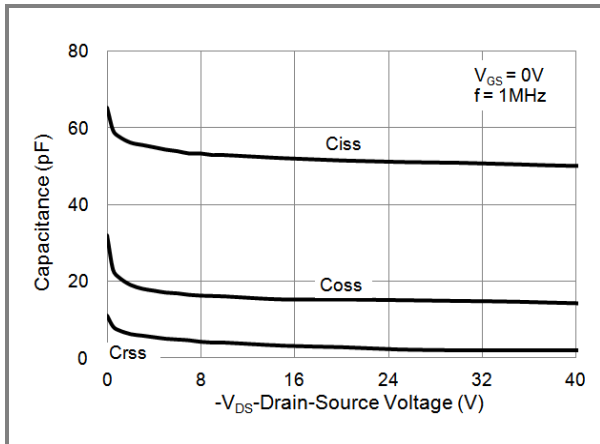


Fig.9 Threshold Voltage Variation with Temperature.

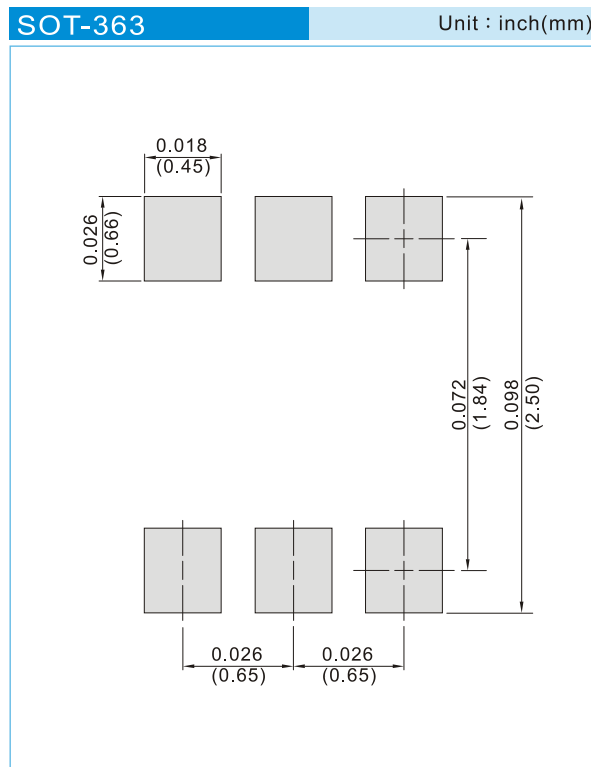


PJT7603

PART NO PACKING CODE VERSION

| Part No Packing Code | Package Type | Packing type | Marking | Version |
|----------------------|--------------|--------------------|---------|--------------|
| PJT7603_R1_00001 | SOT-363 | 3K pcs / 7" reel | T63 | Halogen free |
| PJT7603_R2_00001 | SOT-363 | 10K pcs / 13" reel | T63 | Halogen free |

MOUNTING PAD LAYOUT





PJT7603

Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.